6.12.3 MOSFET, Power, N-Channel

TRANSISTORS, MOSFET, N-CHANNEL, POWER, BASED ON TYPES STRH100N10, STRH40N6, STRH100N6 AND STRH8N10				**303D**
Procurement Specifications	Manufacturer	Nature of Approval	Supervising Authority	Initial Qualification Date
Generic ESCC 5000 Detail ESCC	STMicroectronics Rennes France	Qualification	CNES	Oct 2010
		Remarks		
5205/021, 5205/022, 5205/023, 5205/024				

Qualified range:

5205/021 & 5205/022: Variants 01 and 02 are qualified
5205/023 & 5205/024: Variant 01 is qualified

Package Types:TO-254AA, SMD.5 for STRH40N6 and STRH8N10

Maximum Ratings for 5205/021:

$V_{GS(th)}$	2 –4.5 min/max, I_D=1 mA
$r_{DS(on)}$ (m Ω):	35, V_{GS}=12V, I_D=24A
I_{DS} (A)	48, T_{case} (°C)= +25
V_{DS} (Vdc):	100 over Top , V_{GS}= 0 V
V_{GS} (Vdc):	± 20
P_{TOT}:	170 W at T_{case} ≤+25 C

Operating Temperature Range (°C): -55 to +150

6.12.3 MOSFET, Power, P-Channel

TRANSISTORS, MOSFET, P-CHANNEL, POWER, TYPE STRH40P10 and STRH12P10				**326C**
Procurement Specifications	Manufacturer	Nature of Approval	Supervising Authority	Initial Qualification Date
Generic ESCC 5000 Detail ESCC 5205/025 5205/029	ST Microelectronics Rennes France	Qualification	DLR	Mar 2013
		Remarks These devices have a TID tested capability of 100kRAD(Si).		
Qualified range: Variants 01 and 02 in 5205/025 are qualified. Variants 01 and 02 in 5205/029 are qualified.				